



CRG15T120BK3SD

General Description:

Using HUAJING's proprietary trench design and advanced Field Stop (FS) technology, offering superior conduction and switching performances. RoHS Compliant.

Features:

- FS Trench Technology, Positive temperature coefficient
- Low saturation voltage:

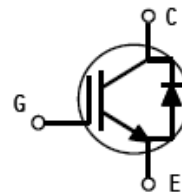
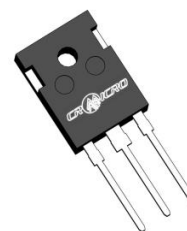
$V_{CE(sat)}$, TYP=2.0V @ $I_C=15A$, $V_{GE}=15V$;

Applications

- Frequency Converter
- Solar Inverter
- UPS

V_{CES}	1200	V
I_C	15	A
P_{tot} ($T_C=25^{\circ}C$)	236	W
$V_{CE(sat)}$	2.0	V

TO-247

**Package Parameters**

Type	Marking	Package	Packing
CRG15T120BK3SD	G15T120BK3SD	TO-247	Tube

Absolute Maximum Ratings ($T_C = 25^\circ\text{C}$ unless otherwise specified):

Symbol	Parameter	Rating	Units
V_{CES}	Collector-Emitter Voltage	1200	V
V_{GES}	Gate- Emitter Voltage	± 20	V
I_C	Collector Current @ $T_C = 25^\circ\text{C}$	30	A
	Collector Current @ $T_C = 100^\circ\text{C}$	15	
I_{CM}^{a1}	Pulsed Collector Current @ $T_C = 25^\circ\text{C}$	45	A
I_F	Diode Continuous Forward Current @ $T_C = 100^\circ\text{C}$	15	A
I_{FM}	Diode Maximum Forward Current	45	A
P_D	Power Dissipation @ $T_C = 25^\circ\text{C}$	236	W
T_J	Operating Junction	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	$-55 \sim 150$	$^\circ\text{C}$
T_L	Maximum Temperature for Soldering	270	$^\circ\text{C}$

a1: Repetitive rating; pulse width limited by maximum junction temperature

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Thermal Resistance, Junction to case for IGBT		0.53	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient for IGBT		27.1	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance, Junction to case for FRD		0.69	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient for FRD		35.5	

Electrical Characteristics of the IGBT ($T_C = 25^\circ\text{C}$ unless otherwise specified):

Symbol	Parameter	Test Conditions	SPEC			Un its
			Min.	Typ.	Max.	
OFF Characteristics						
V _{(BR)CES}	Collector-Emitter Breakdown Voltage	V _{GE} =0V,I _{CE} =250uA	1200	--	--	V
I _{CES}	Collector-Emitter Leakage Current	V _{GE} =0V,V _{CE} =1200V	--	--	1.0	mA
I _{GES(F)}	Gate to Emitter Forward Leakage	V _{GE} =+20V	--	--	+250	nA
I _{GES(R)}	Gate to Source Reverse Leakage	V _{GE} =-20V	--	--	-250	nA
ON Characteristics						
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C =15A ,V _{GE} =15V	--	2.0	2.5	V
V _{GE(th)}	Gate Threshold Voltage	I _C =250u A ,V _{CE} =V _{GE}	4.0	5.8	7.5	V
Pulse width tp≤300μs,δ≤2%						
Dynamic Characteristics						
C _{ies}	Input Capacitance	V _{CE} =25V,V _{GE} =0V f=1MHz	--	1207	--	pF
C _{oes}	Output Capacitance		--	58	--	
C _{res}	Reverse Transfer Capacitance		--	26	--	
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{CE} =600V,I _C =15A,	--	35	--	ns
t _r	Rise Time	R _g =10 Ω ,V _{GE} =15V,	--	30	--	

t _{d(off)}	Turn-Off Delay Time	Inductive Load, T _J =25℃,	--	100	--	mJ
t _f	Fall Time		--	67	--	
E _{on}	Turn-On Switching Loss		--	1.03	--	
E _{off}	Turn-Off Switching Loss		--	0.30	--	
E _{ts}	Total Switching Loss		--	1.33	--	
t _{d(on)}	Turn-on Delay Time	V _{CE} =600V,I _C =15A, R _g =10 Ω,V _{GE} =15V, Inductive Load, T _J =150℃	--	33	--	ns
t _r	Rise Time		--	33	--	
t _{d(off)}	Turn-Off Delay Time		--	108	--	
t _f	Fall Time		--	103	--	
E _{on}	Turn-On Switching Loss		--	1.05	--	mJ
E _{off}	Turn-Off Switching Loss	--	0.49	--		
E _{ts}	Total Switching Loss	--	1.54	--		
Q _g	Total Gate Charge	V _{CE} =600V,I _C =15A, V _{GE} =15V,	--	75	--	nC
Q _{ge}	Gate to Emitter Charge		--	11	--	
Q _{gc}	Gate to Collector Charge		--	44	--	
Electrical Characteristics of the DIODE (T _C = 25℃ unless otherwise specified):						
V _F	Diode Forward Voltage	I _F =15A	--	2.1	3.2	V
t _{rr}	Reverse Recovery Time	I _F =15A di/dt=200A/uS	--	50	--	ns
I _{rrm}	Reverse Recovery Current		--	5	--	A
Q _{rr}	Reverse Recovery Charge		--	139	--	nC

Typical Performance Characteristics

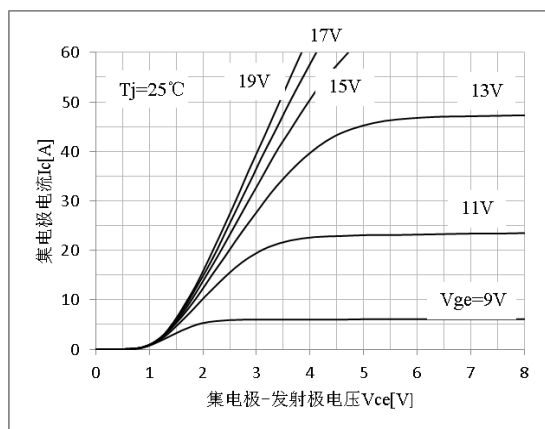


Figure 1. Output Characteristics

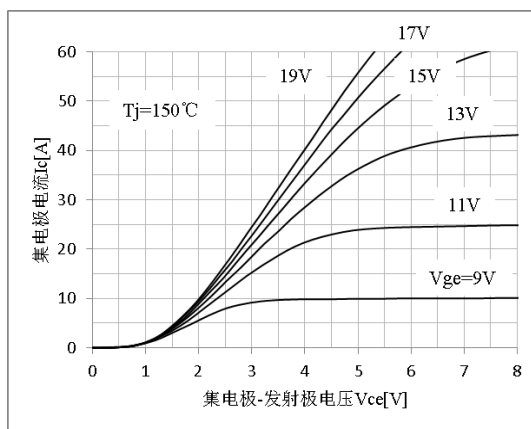


Figure 2. Output Characteristics

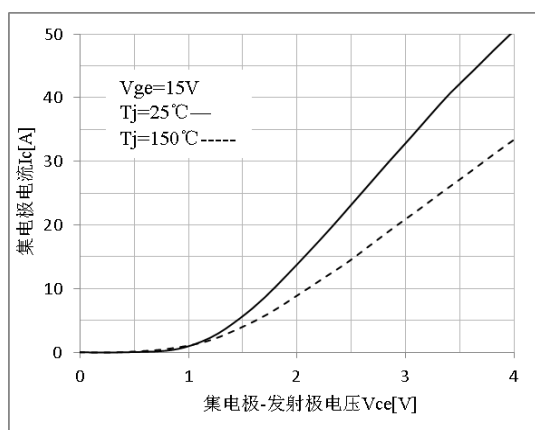


Figure 3. Saturation Voltage Characteristics

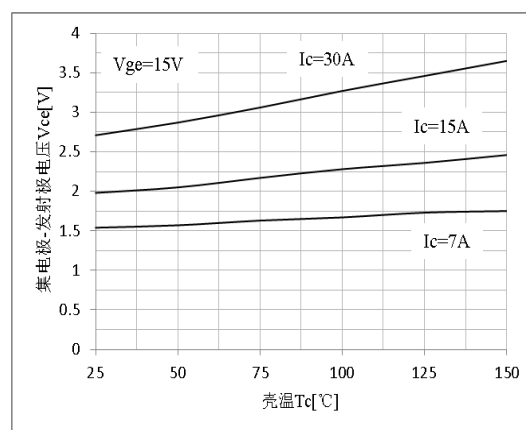


Figure 4. Saturation Voltage -T_c Characteristics

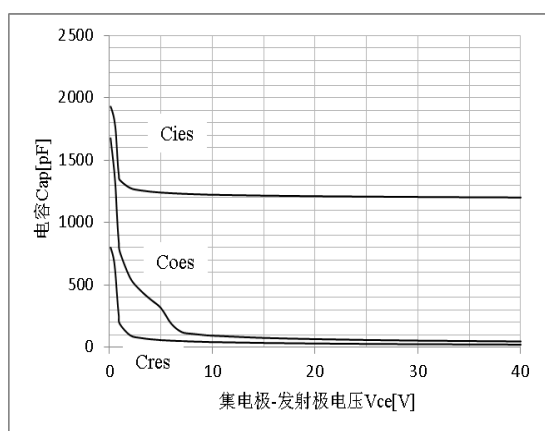


Figure 5. Capacitance Characteristics

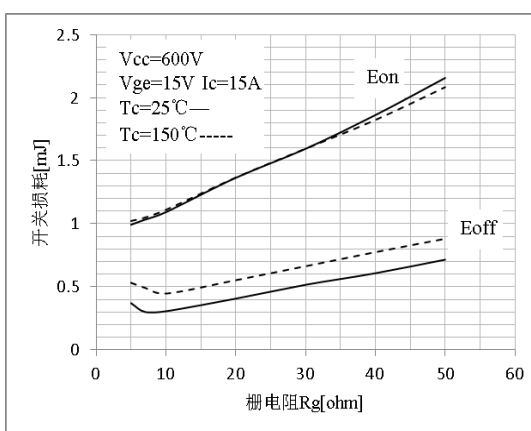
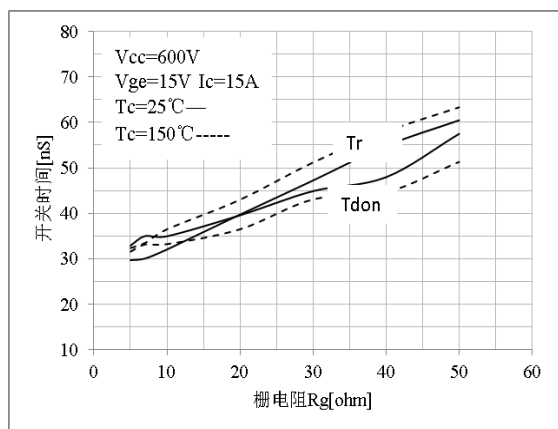
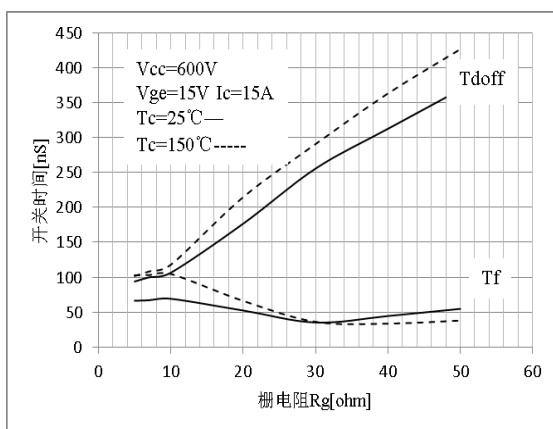
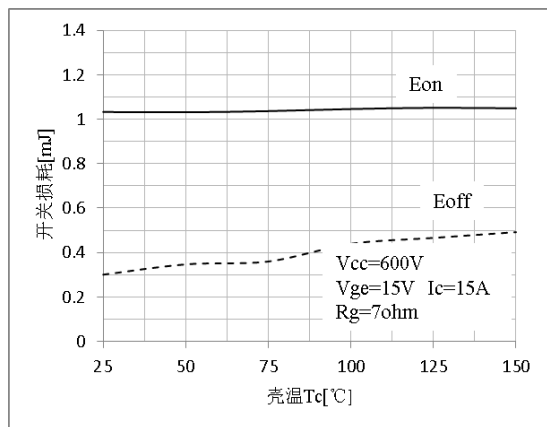
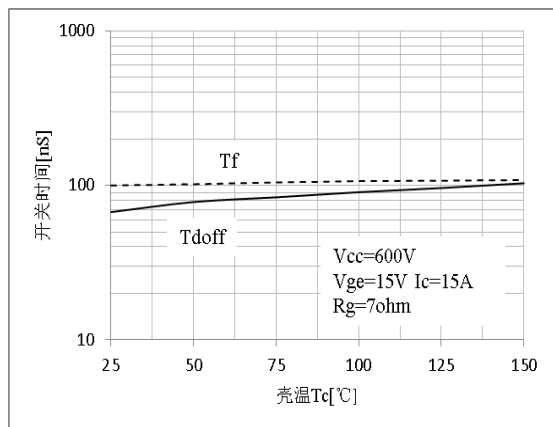
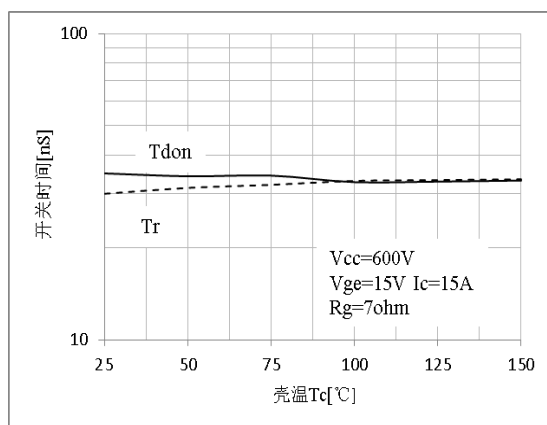
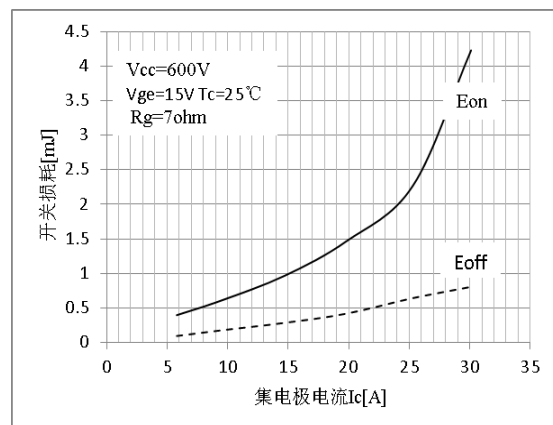
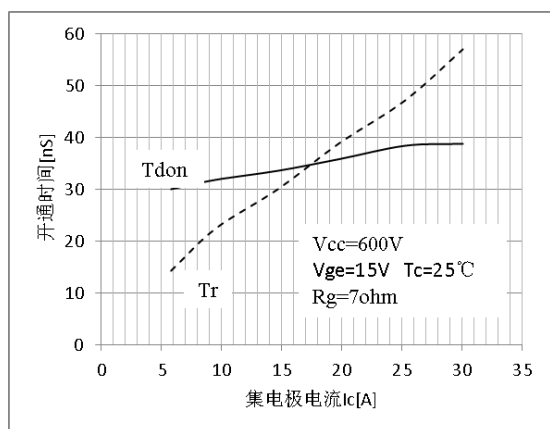
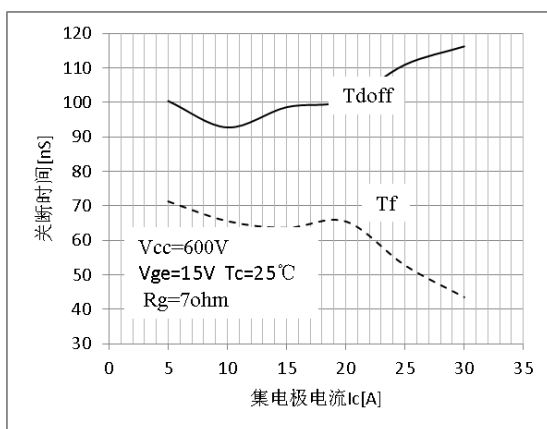
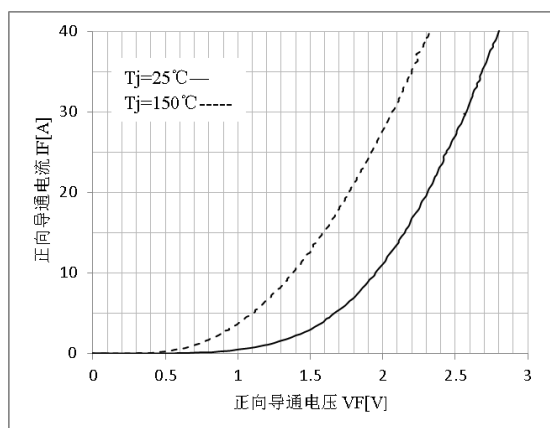
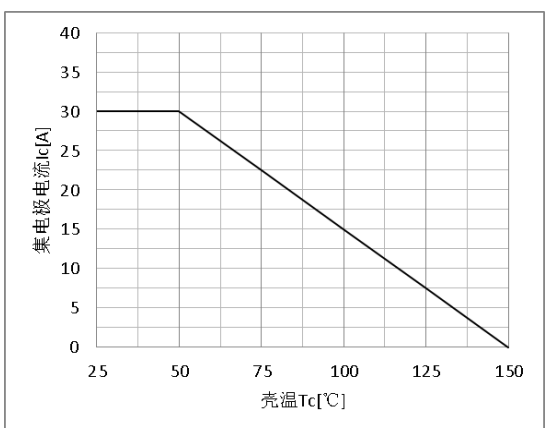
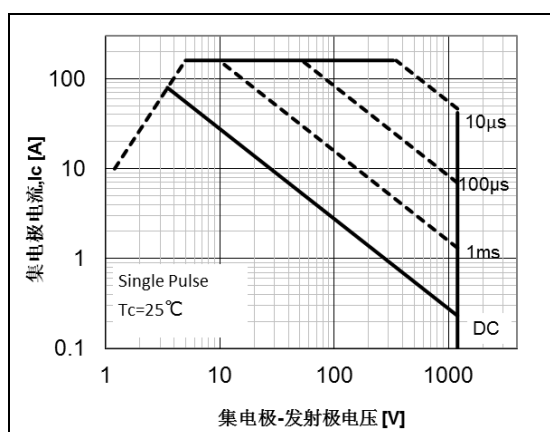
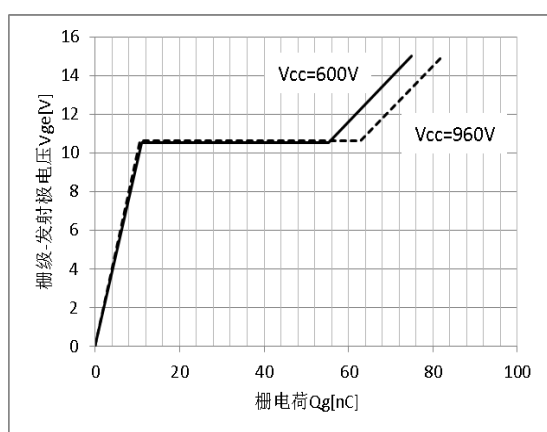


Figure 6. Switching Loss-R_g Characteristics


Figure 7.Switching Time- R_g Characteristics

Figure 8.Switching Time- R_g Characteristics

Figure 9.Switching Loss- T_c Characteristics

Figure 10. Turn-Off Time- T_c Characteristics

Figure 11. Turn-On Time- T_c Characteristics

Figure 12.Switching Loss- I_c Characteristics


Figure 13. Turn-On Time-Ic Characteristics

Figure 14. Turn-Off Time-Ic Characteristics

Figure 15. Diode Forward Characteristics

Figure 16. Collector Current-Tc Characteristics

Figure 17. Forward Bias Safe Operating Area

Figure 18. Gate Charge Characteristics

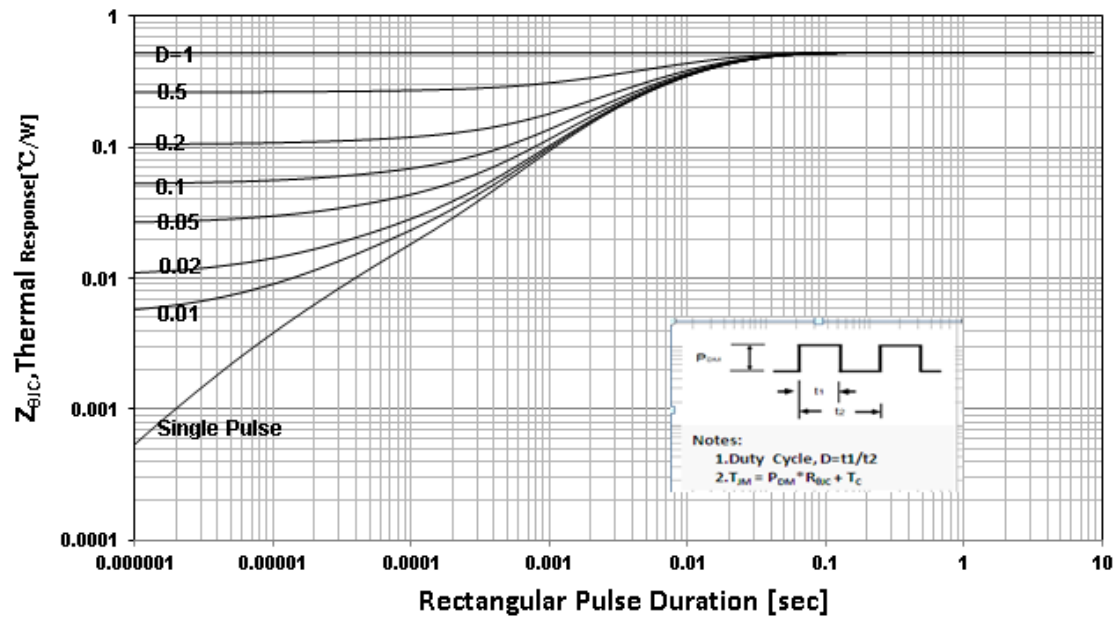
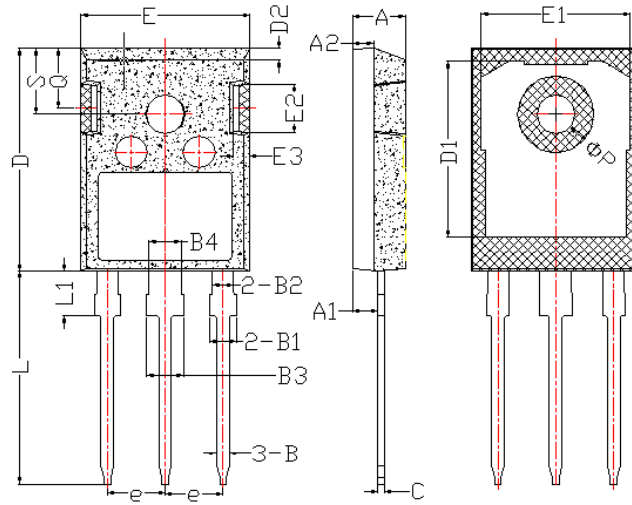


Figure 19.IGBT Transient Thermal Impedance

Package Information



Items	Values (mm)	
	MIN	MAX
A	4.6	5.2
A1	2.2	2.6
B	0.9	1.4
B1	1.75	2.35
B2	1.75	2.15
B3	2.8	3.35
B4	2.8	3.15
C	0.5	0.7
D	20.60	21.30
D1	16	18
E	15.5	16.10
E1	13	14.7
E2	3.80	5.3
E3	0.8	2.60
e	5.2	5.7
L	19	20.5
L1	3.9	4.6
ΦP	3.3	3.70
Q	5.2	6.00
S	5.8	6.6

TO-247 Package

**The name and content of poisonous and harmful material in products**

Part's Name Limit	Hazardous Substance									
	Pb	Hg	Cd	Cr(VI)	PBB	PBDE	DIBP	DEHP	DBP	BBP
	≤0.1%	≤0.1%	≤ 0.01%	≤0.1%	≤0.1%	≤0.1%	≤0.1%	≤0.1%	≤0.1%	≤0.1%
Lead Frame	○	○	○	○	○	○	○	○	○	○
Molding	○	○	○	○	○	○	○	○	○	○
Chip	○	○	○	○	○	○	○	○	○	○
Wire Bonding	○	○	○	○	○	○	○	○	○	○
Solder	×	○	○	○	○	○	○	○	○	○
Note	○: Means the hazardous material is under the criterion of 2011/65/EU. ×: Means the hazardous material exceeds the criterion of 2011/65/EU. The plumbum element of solder exist in products presently, but within the allowed range of Eurogroup's RoHS.									

Warnings

1. Exceeding the maximum ratings of the device in performance may cause damage to the device, even the permanent failure, which may affect the dependability of the machine. It is suggested to be used under 80 percent of the maximum ratings of the device.
2. When installing the heat sink, please pay attention to the torsional moment and the smoothness of the heat sink.
3. IGBTs is the device which is sensitive to the static electricity, it is necessary to protect the device from being damaged by the static electricity when using it.
4. This publication is made by Huajing Microelectronics and subject to regular change without notice.

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